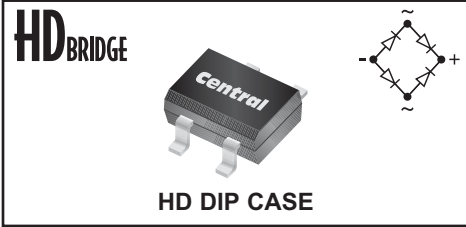


CBRHDSH1-60
SURFACE MOUNT
HIGH DENSITY
1 AMP SILICON
SCHOTTKY BRIDGE RECTIFIER



www.centralemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHDSH1-60 is a full wave bridge rectifier mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

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FEATURES:

- Low Leakage Current (7.0 μ A TYP @ V_{RRM})
- High 1.0A Current Rating
- Low V_F Schottky Diodes (600mV MAX @ $I_F=1.0A$)

MAXIMUM RATINGS: ($T_A=25^{\circ}C$ unless otherwise noted)		SYMBOL		UNITS
Peak Repetitive Reverse Voltage		V_{RRM}	60	V
DC Blocking Voltage		V_R	60	V
RMS Reverse Voltage		$V_{R(RMS)}$	42	V
Average Forward Current		I_O	1.0	A
Peak Forward Surge Current		I_{FSM}	20	A
Power Dissipation		P_D	1.2	W
Operating Junction Temperature		T_J	-50 to +125	$^{\circ}C$
Storage Temperature		T_{stg}	-50 to +150	$^{\circ}C$
Thermal Resistance		Θ_{JA}	85	$^{\circ}C/W$

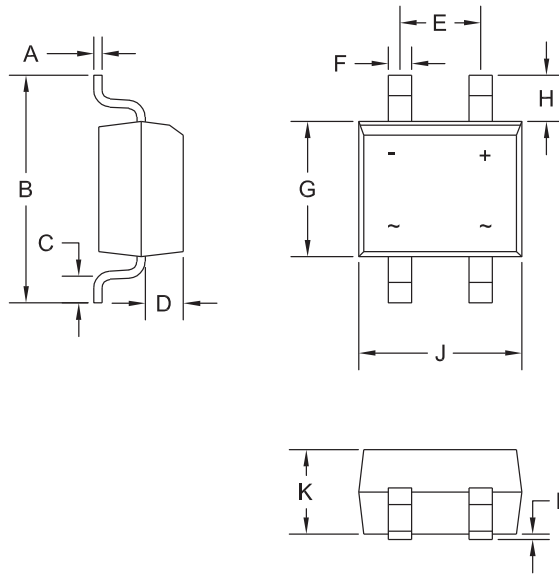
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=60V$	7.0	20	μA
I_R	$V_R=60V, T_A=100^{\circ}C$	2.0	10	mA
V_F	$I_F=500mA$	430	500	mV
V_F	$I_F=1.0A$	500	600	mV
C_J	$V_R=4.0V, f=1.0MHz$	130		pF

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HD DIP CASE - MECHANICAL OUTLINE



R2

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.275	-	7.00
C	0.027	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.090	0.106	2.30	2.70
F	0.019	0.031	0.50	0.80
G	0.150	0.165	3.80	4.20
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.090	0.106	2.30	2.70
L	0.000	0.008	0.00	0.20

HD DIP (REV: R2)

MARKING CODE: CSH106

R2 (4-January 2010)